

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------|------------------|
| 1 | 75 | (porous near (silica (silicon adj (oxide dioxide)))) and ("low-k" "low k" (low adj (permittivity dielectric))) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/21 14:44 |
| 2 | 99 | (438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((porous near (silica (silicon adj (oxide dioxide)))) same ("low-k" "low k" (low adj (permittivity dielectric)))) | USPAT; US-PGPUB | 2004/08/21 14:58 |
| - | 8022 | 438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls. | USPAT; US-PGPUB | 2004/08/20 16:09 |
| - | 4776 | (interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric))) | USPAT; US-PGPUB | 2004/08/20 18:17 |
| - | 1106 | (438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) | USPAT; US-PGPUB | 2004/08/20 16:21 |
| - | 821 | (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6) | USPAT; US-PGPUB | 2004/08/20 16:22 |
| - | 342 | (porous near (silica (silicon adj (oxide dioxide)))) same ("low-k" "low k" (low adj (permittivity dielectric))) | USPAT; US-PGPUB | 2004/08/20 16:28 |
| - | 151 | (438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (hmds hexamethyldisilazane (silane adj coupler) (metal adj coupler)) | USPAT; US-PGPUB | 2004/08/20 16:34 |
| - | 11 | (transistor fet mos mosfet (field adj effect)) same (gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact) same (trace wir\$6 line interconnect\$6) | USPAT; US-PGPUB | 2004/08/20 16:35 |
| - | 11 | (transistor fet mos mosfet (field adj effect) gate source drain) and (liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/20 16:41 |
| - | 139 | (transistor fet mos mosfet (field adj effect) gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6) | USPAT; US-PGPUB | 2004/08/20 16:45 |
| - | 93 | (liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/20 17:22 |
| - | 291 | (438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6)) | USPAT; US-PGPUB | 2004/08/20 18:15 |
| - | 441 | borderless near contact | USPAT; US-PGPUB | 2004/08/20 18:17 |
| - | 219 | borderless near contact | EPO; JPO; DERWENT; IBM_TDB | 2004/08/20 18:17 |

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| - | 0 | (borderless near contact) and (interlayer ild imd organic porous) and ("low-k" "low k" (low adj (permittivity dielectric))) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/20 18:18 |
| - | 0 | (borderless near contact) and ("low-k" "low k" (low adj (permittivity dielectric))) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/20 18:18 |
| - | 36 | ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and ((438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (hmds hexamethyldisilazane (silane adj coupler) (metal adj coupler))) | USPAT; US-PGPUB | 2004/08/20 18:32 |
| - | 15 | ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (borderless near contact) | USPAT; US-PGPUB | 2004/08/20 18:38 |
| - | 8 | (borderless near contact) same ("low-k" "low k" (low adj (permittivity dielectric))) | USPAT; US-PGPUB | 2004/08/20 18:46 |
| - | 50 | (borderless near contact) and (interlayer ild imd organic porous) | EPO; JPO; DERWENT; IBM_TDB | 2004/08/20 18:51 |
| - | 72 | (438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (borderless near contact) | USPAT; US-PGPUB | 2004/08/20 18:56 |